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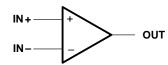
- A-Suffix Versions Offer 5-mV VIO
- B-Suffix Versions Offer 2-mV VIO
- Wide Range of Supply Voltages 1.4 V to 16 V
- **True Single-Supply Operation**
- Common-Mode Input Voltage Includes the **Negative Rail**
- Low Noise . . . 30 nV/ \sqrt{Hz} Typ at f = 1 kHz (High-Bias Versions)

D. P. OR PW PACKAGE (TOP VIEW) **10UT** ∏ V_{DD}] 20UT 1IN-1IN+ **∏** 3 ∏ 2IN− V_{DD}_/GND 2IN+

symbol (each amplifier)

description

The TLC252, TLC25L2, and TLC25M2 are low-cost, low-power dual operational amplifiers designed to operate with single or dual supplies. These devices utilize the Texas Instruments



silicon gate LinCMOS™ process, giving them stable input offset voltages that are available in selected grades of 2, 5, or 10 mV maximum, very high input impedances, and extremely low input offset and bias currents. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this series is ideally suited for battery-powered or energy-conserving applications. The series offers operation down to a 1.4-V supply, is stable at unity gain, and has excellent noise characteristics.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in a degradation of the device parametric performance.

AVAILABLE OPTIONS

	Viemax		PACKAGED DEVICES		CHIP FORM
TA	V _{IO} max AT 25°C	SMALL OUTLINE PLASTIC DIP (D) (P)		TSSOP (PW)	(Y)
	10 mV 5 mV 2 mV	TLC252CD TLC252ACD TLC252BCD	TLC252CP TLC252ACP TLC252BCP	TLC252CPW TLC252ACPW TLC252BCPW	TLC252Y — —
0°C to 70°C	10 mV 5 mV 2 mV	TLC25L2CD TLC25L2ACD TLC25L2BCD	TLC25L2CP TLC25L2ACP TLC25L2BCP	TLC25L2CPW TLC25L2ACPW TLC25L2BCPW	TLC25L2Y — —
	10 mV 5 mV 2 mV	TLC25M2CD TLC25M2ACD TLC25M2BCD	TLC25M2CP TLC25M2ACP TLC25M2BCP		TLC25M2Y — —

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC252CDR). Chips are tested at 25°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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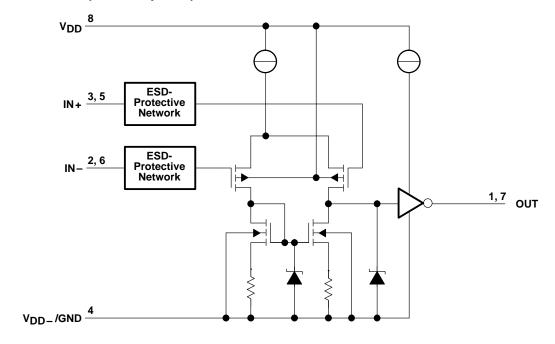
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description (continued)

Because of the extremely high input impedance and low input bias and offset currents, applications for the TLC252/25_2 series include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOS™ operational amplifiers without the power penalties of traditional bipolar devices. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are all easily designed with the TLC252/25_2 series devices. Remote and inaccessible equipment applications are possible using their low-voltage and low-power capabilities. The TLC252/25_2 series is well suited to solve the difficult problems associated with single-battery and solar-cell-powered applications. This series includes devices that are characterized for the commercial temperature range and are available in 8-pin plastic dip and the small-outline package. The device is also available in chip form.

The TLC252/25_2 series is characterized for operation from 0°C to 70°C.

equivalent schematic (each amplifier)

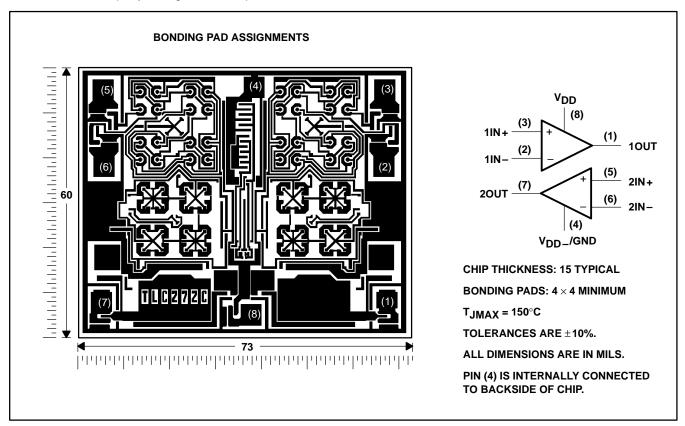




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TLC252Y, TLC25L2Y, and TLC25M2Y chip information

These chips, properly assembled, display characteristics similar to the TLC252/25_2. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage, V _{ID} (see Note 2)	±18 V
Input voltage range, V _I (any input)	0.3 V to 18 V
Duration of short circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD}_/GND.
 - 2. Differential voltages are at IN+, with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW
PW	525 mW	4.2 mW/°C	336 mW

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V _{DD}		1.4	16	V
ommon-mode input voltage, V _{IC}	V _{DD} = 1.4 V	0	0.2	
	V _{DD} = 5 V	-0.2	4	\ _{\/}
Common-mode input voltage, v _{IC}	V _{DD} = 10 V	-0.2	9	l v
	V _{DD} = 16 V	-0.2	14	
Operating free-air temperature, TA		0	70	°C



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electrical characteristics at specified free-air temperature, $V_{DD} = 1.4 \text{ V}$ (unless otherwise noted)

	PARAME	TED	TEST CONDITION	ıct	TL	.C252_	С	TL	C25L2	_C	TL	C25M2	_C	UNIT
	PARAME	IEK	TEST CONDITION	NS1	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
				25°C			10			10			10	
		TLC25_2C		0°C to 70°C			12			12			12	
	Input		V _O = 0.2 V,	25°C			5			5			5	
VIO	offset voltage	TLC25_2AC	$R_S = 50 \Omega$	0°C to 70°C			6.5			6.5			6.5	mV
				25°C			2			2			2	
		TLC25_2BC		0°C to 70°C			3			3			3	
ανιο	-	temperature nt of input tage		25°C to 70°C		1			1			1		μV/°C
				25°C		1	60		1	60		1	60	
lio	Input offs	et current	V _O = 0.2 V	0°C to 70°C			300			300			300	pА
				25°C		1	60		1	60		1	60	
I _{IB}	Input bias	s current	V _O = 0.2 V	0°C to 70°C			600			600			600	pА
VICR	Common voltage ra	i-mode input ange		25°C	0 to 0.2			0 to 0.2			0 to 0.2			V
Vом	Peak out swing‡	put voltage	V _{ID} = 100 mV	25°C	450	700		450	700		450	700		mV
A _{VD}	Large-sig differentia amplifica	al voltage	V_O = 100 to 300 mV, R_S = 50 Ω	25°C		10			20			20		V/mV
CMRR	Common rejection		$V_O = 0.2 \text{ V},$ $V_{IC} = V_{ICR} \text{min}$	25°C	60	77		60	77		60	77		dB
I _{DD}	Supply co	urrent	V _O = 0.2 V, No load	25°C		300	375		25	34		200	250	μА

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following value: for low bias $R_L = 1 \text{ M}\Omega$, for medium bias $R_L = 100 \text{ k}\Omega$.

operating characteristics, V_{DD} = 1.4 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	TI	LC252_	С	TL	C25L2_	C	TLO	C25M2_	C	UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
B ₁	Unity-gain bandwidth	$A_V = 40 \text{ dB},$ $C_L = 10 \text{ pF},$ $R_S = 50 \Omega$		12			12			12		kHz
SR	Slew rate at unity gain	See Figure 1		0.1			0.001			0.01		V/μs
	Overshoot factor	See Figure 1		30%			35%			35%		

[‡] The output swings to the potential of V_{DD}_/GND.

electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST COND	ITIONS	T _A †		C, TLC2 C252B0		UNIT
					,	MIN	TYP		
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1102520	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			12	
\/10	Input offset voltage	TLC252AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
VIO	input onset voltage	TLO252AC	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC252BC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.23	2	
		TLC252BC	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			3	
ανιο	Average temperature coeff input offset voltage	icient of			25°C to 70°C		1.8		μV/°C
1	Innut offeet ourrent (eee Ne	oto 4\	V- 25V	V:- 2.5.V	25°C		0.1	60	~ ^
ΙΟ	Input offset current (see No	ote 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	70°C		7	300	pА
1	Input bias current (see Not	0.4)	V _O = 2.5 V,	V:= - 2 5 V	25°C		0.6	60	Aq
ΙΒ	input bias current (see Not	e 4)	ν _O = 2.5 ν,	$V_{IC} = 2.5 V$	70°C		40	600	рA
	Common-mode input volta	ne.			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	VICR Common-mode input voltage range (see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	3.8		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	0°C	3	3.8		V
					70°C	3	3.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	5	23		
A_{VD}	Large-signal differential volume	Itage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	0°C	4	27		V/mV
	атриновнот				70°C	4	20		
					25°C	65	80		
CMRR	Common-mode rejection ra	atio	V _{IC} = V _{ICR} min		0°C	60	84		dB
					70°C	60	85		
	0 1 1 1				25°C	65	95		
ksvr	Supply-voltage rejection ra (ΔVDD/ΔVDD)	tio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	94		dB
	/טטי ^ב יטטי 				70°C	60	96		
			V- 25V	V:- 25V	25°C		1.4	3.2	
I_{DD}	Supply current (two amplifi	ers)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V,$	0°C		1.6	3.6	mA
					70°C		1.2	2.6	

†Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONE	DITIONS	T _A †	TLC252	C, TLC2 .C252B0		UNIT
						MIN	TYP	MAX 10 12 5 6.5 2 3 60 300 60 600 50 50	
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLC252C	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC252AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV μV/°C pA V V W V dB dB
۷IO	input onset voltage	TLUZUZAU	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC252BC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.29	2	
		TLC252BC	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			3	
αVIO	Average temperature coeffi offset voltage	cient of input			25°C to 70°C		2		μV/°C
l. a	Innut offeet ourrent (see No	.to 4\	Va 25V	\/ 0.E.\/	25°C		0.1	60	π Λ
ΙO	Input offset current (see No	nte 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	70°C		7	300	PΑ
1	Input higo ourrent (see Not	2.4)	V= -25V	V _{IC} = 2.5 V	25°C		0.6	60	nΛ
IB	Input bias current (see Note	₹4)	$V_0 = 2.5 \text{ V},$	vIC = 5.5 v	70°C		50	600	PΑ
						-0.2	-0.3		
					25°C	to 9	to 9.2		V
VICR	Common-mode input voltage range (see Note 5)	ge				-0.2	9.2		
	rango (oco rroto o)				Full range	to			V
						8.5			
					25°C	8	8.5		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	0°C	8	8.5		V
					70°C	7.8	8.4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOT = 0	0°C		0	50	mV
					70°C		0	50	
	l anno aimeal differential cal	.			25°C	10	36		
A_{VD}	Large-signal differential vol amplification	tage	$V_0 = 1 V to 6 V$,	$R_L = 10 \text{ k}\Omega$	0°C	7.5	42		V/mV
					70°C	7.5	32		
					25°C	65	85		
CMRR	Common-mode rejection ra	ntio	V _{IC} = V _{ICR} min		0°C	60	88		dB
					70°C	60	88		
	Owner by sealth and the				25°C	65	95		
ksvr	Supply-voltage rejection rate (ΔVDD/ΔVDD)	IIO	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 V$	0°C	60	94		dB
	עוטי-יטטי				70°C	60	96		
				\/ <u> </u>	25°C		1.9	4	
I_{DD}	Supply current (two amplifiers)		$V_O = 5 V$, V	V _{IC} = 5 V,	0°C		2.3	4.4	4 mA
					70°C		1.6	3.4	1

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER		TEST CONDITION	ONS	TA	TLC252	C, TLC2 .C252B0		UNIT
						MIN	TYP	MAX	
					25°C		3.6		
				V _{I(PP)} = 1 V	0°C		4		
SR	Slew rate at unity gain	$R_L = 10 \text{ k}\Omega$,	$C_L = 20 pF$,		70°C		3		\//ua
J SK	Siew rate at unity gain	See Figure 1			25°C		2.9		V/μs
				$V_{I(PP)} = 2.5 V$	0°C		3.1		
				70°C		2.5			
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		25		nV/√ Hz
					25°C		320		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega$,	0°C		340		kHz
		occ r igure			70°C		260		
					25°C		1.7		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		2		MHz
					70°C		1.3		
		\/ 40 ···\/	, D	0 00 - 5	25°C		46°		
φm	Phase margin		$V_I = 10 \text{ mV}, \qquad f = B_1, \qquad C_L = 20 \text{ pF},$ See Figure 3		0°C		47°		
		Seeguic o			70°C		43°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER		TEST CONDITI	ONS	TA	TLC2520	C, TLC2 C252B0	-	UNIT
				_		MIN	TYP	MAX	
					25°C		5.3		
				V _{I(PP)} = 1 V	0°C		5.9		
CD.	Class rate at units rain	$R_L = 10 \text{ k}\Omega$,	$C_L = 20 pF$,		70°C		4.3		\ \//\\\c
SR	Slew rate at unity gain	See Figure 1 25°C 4.6		V/μs					
				$V_{I(PP)} = 5.5 V$	0°C		5.1		
					70°C		3.8		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		25		nV/√ Hz
					25°C		200		
Вом	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega$,	0°C		220		kHz
		See rigule r			70°C		140		
					25°C		2.2		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		2.5		MHz
					70°C		1.8		
		V 40 V	. 5	0 00 5	25°C		49°		
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	0°C		50°]
		Seeguic o			70°C		46°		<u> </u>

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL	LC25L20 .C25L2A .C25L2B	С	UNIT
						MIN	TYP	MAX	
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLG252G	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	
\ _{\\\}	Input offset voltage	TLC252AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
VIO	Input offset voltage	TLCZSZAC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	IIIV
		TLC252BC	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		0.204	2	
		TLCZSZBC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3	
αVIO	Average temperature coe input offset voltage	fficient of			25°C to 70°C		1.1		μV/°C
1	Innut offeet ourrent (e.e. N	loto 4)	V- 25V	V 2.5.V	25°C		0.1	60	~ Λ
lio	Input offset current (see N	10te 4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	70°C		7	300	pΑ
1	lanut bina aumant (ana Na	-t 4\	V- 05V	V 0.5.V	25°C		0.6	60	^
lΒ	Input bias current (see No	ote 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	70°C		50	600	pΑ
	Common-mode input volt	age			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	range (see Note 5)	· • • •		Full range	-0.2 to 3.5			V	
					25°C	3.2	4.1		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	0°C	3	4.1		V
					70°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
		1-			25°C	50	700		
AVD	Large-signal differential vi amplification	oltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	0°C	50	700		V/mV
	ampilioation				70°C	50	380		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	V _{IC} = V _{ICR} min		0°C	60	95		dB
					70°C	60	95		
	0 1 1				25°C	70	97		
k _{SVR}	Supply-voltage rejection r (ΔV _{DD} /ΔV _{DD})	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	97		dB
	עטטי∸יטטי/				70°C	60	98		
			Vo = 2.5.V	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	25°C		20	34	
I_{DD}	Supply current (two ampli	fiers)	V _O = 2.5 V, No load	vIC = 5.5 v,	0°C		24	42	μΑ
					70°C		16	28	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL	_C25L20 C25L2A C25L2B	С	UNIT
						MIN	TYP	MAX	
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1102320	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	
\/\c	Input offset voltage	TLC252AC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	mV
VIO	input onset voltage	TLUZUZAC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	IIIV
		TLC252BC	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		0.235	2	
		TLOZUZBO	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3	
αVIO	Average temperature coef input offset voltage	ficient of			25°C to 70°C		1		μV/°C
1	Input offset ourrest (see N	oto 4)	V _O = 5 V,	V F V	25°C		0.1	60	- Δ
10	Input offset current (see N	ote 4)	vO = 5 v,	$V_{IC} = 5 V$	70°C		8	300	pΑ
1	Innut him ourrent (and No	to 4)	V- 5.V	V:- EV	25°C		0.7	60	~^
IВ	Input bias current (see No	te 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		50	600	pΑ
	Common-mode input volta	age			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)				Full range	-0.2 to 8.5		0.3 to 9.2	V
					25°C	8	8.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	0°C	7.8	8.9		V
					70°C	7.8	8.9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOT = 0	0°C		0	50	mV
					70°C		0	50	
	Large-signal differential vo	ltogo			25°C	50	860		
AVD	amplification	maye	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	0°C	50	1025		V/mV
					70°C	50	660		
					25°C	65	97		
CMRR	Common-mode rejection r	atio	V _{IC} = V _{ICR} min		0°C	60	97		dB
					70°C	60	97		
	Cumply volters as as as the same				25°C	70	97		
ksvr	Supply-voltage rejection ra (ΔVDD/ΔVDD)	auO	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	97		dB
					70°C	60	98		
			V _O = 5 V,	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	25°C		29	46	
IDD	Supply current (two amplif	iers)	VO = 5 V, No load	$V_{IC} = 5 V$,	0°C		36	66	μΑ
					70°C		22	40	

[†]Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 V$

	PARAMETER		TEST CONDITION	ONS	TA	TL TL(С	UNIT	
						MIN	TYP	MAX	
					25°C		0.03		
				V _{I(PP)} = 1 V	0°C		0.04		
SR	Slow rate at unity gain	$R_L = 1 M\Omega$,	$C_L = 20 pF$,		70°C		0.03		\//uo
J SK	Slew rate at unity gain	See Figure 1			25°C		0.03		V/μs
				$V_{I(PP)} = 2.5 V$	0°C		0.03		
				1 ' '	70°C		0.02		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		68		nV/√ Hz
		., .,		5 (110	25°C		5		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure	$C_L = 20 pF$,	$R_L = 1 M\Omega$,	0°C		6		kHz
	barrawian	occ r igure			70°C		4.5		
					25°C		85		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		100		MHz
	A Phase margin				70°C		65		
		V 40V	(5	0 00 - 5	25°C		34°		
φm		V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	0°C		36°		
		garo			70°C		30°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER		TEST CONDITION	ONS	TA	TL	.C25L20 C25L2A C25L2B	С	UNIT
						MIN	TYP	MAX	
					25°C		0.05		
				V _{I(PP)} = 1 V	0°C		0.05		
SR	Slew rate at unity gain	$R_L = 1 M\Omega$,	$C_L = 20 pF$,		70°C		0.04		V/μs
J SK	Siew rate at unity gain	See Figure 1			25°C	0.04 0.05			ν/μ5
				$V_{I(PP)} = 5.5 V$	0°C				
					70°C		0.04		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		68		nV/√ Hz
					25°C	1			
ВОМ	Maximum output-swing bandwidth	VO = VOH, See Figure 1	$C_L = 20 pF$,	$R_L = 1 M\Omega$,	0°C		1.3		kHz
	bariawiatri	occ rigare r			70°C		0.9		
					25°C		110		
В1	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		125		MHz
					70°C		90		
		V 40V	(5	0 00 - 5	25°C		38°		
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	0°C		40°		
					70°C		34°		

electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONE	DITIONS	T _A †	TLO	.C25M20 C25M2A C25M2B	C	UNIT
						MIN	TYP	MAX	
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1LC252C	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC252AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
VIO	input onset voltage	TLO252AC	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC252BC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.22	2	
		12020250	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3	
αVIO	Average temperature coef input offset voltage	ficient of			25°C to 70°C		1.7		μV/°C
1	Input offset current (see N	oto 4)	V _O = 2.5 V,	V _{IC} = 2.5 V	25°C		0.1	60	ρĄ
lio	input onset current (see N	ote 4)	VO = 2.5 V,	vIC = 5.5 v	70°C		7	300	pΑ
l.s	Input bigg ourrent (see No	to 4)	Vo - 2.5.V	\/.o = 2.5.\/	25°C		0.6	60	- Α
IB	Input bias current (see No	te 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		40	600	pА
	Common-mode input volta	age			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	range (see Note 5)	.go			Full range	-0.2 to 3.5			٧
					25°C	3.2	3.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	0°C	3	3.9		V
					70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
	l anno ainmal differential co	lt			25°C	25	170		
AVD	Large-signal differential vo amplification	ntage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	0°C	15	200		V/mV
					70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection r	atio	V _{IC} = V _{ICR} min		0°C	60	91		dB
					70°C	60	92		
	Cupply voltage rejection	atio			25°C	70	93		
ksvr	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{DD})$	่งเเ∪	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB
				-	70°C	60	94		
				V10 - 25 V	25°C		210	560	
IDD	Supply current (two amplif	$V_O = 2.5 \text{ V},$ No load	V _{IC} = 2.5 V,	0°C		250	640	⊣ '	
Ļ			140 1000		70°C		170	440	

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER	TEST CONI	DITIONS	T _A †	TL	.C25M20 C25M2A C25M2B	C	UNIT	
						MIN	TYP	MAX	
		TLC252C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1LC252C	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	
V _{IO}	Input offset voltage	TLC252AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
I VIO	Input offset voltage	TLUZSZAU	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC252BC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.224	2	
		TEGZSZBC	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3	
αVIO	Average temperature coe input offset voltage	fficient of			25°C to 70°C		2.1		μV/°C
1	Input offset surrent (see A	loto 4)	V - E V	\/ E\/	25°C		0.1	60	- A
10	Input offset current (see N	10te 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	70°C		7	300	pΑ
	Innut high current (one No	sto 4)	V- 5.V	\/ E\/	25°C		0.7	60	- A
ΙΒ	Input bias current (see No	ne 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		50	600	pА
	Common-mode input volta	age			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)	9-			Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV}, R_L = 100 \text{ kg}$		0°C	7.8	8.7		V
					70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
	l anno airmal differential	-14			25°C	25	275		
AVD	Large-signal differential vo amplification	oitage	$V_0 = 1 \ V \text{ to 6 V},$	$R_L = 100 \text{ k}\Omega$	0°C	15	320		V/mV
					70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	$V_{IC} = V_{ICR}min$		0°C	60	94		dB
					70°C	60	94		
	Cumply volters == !==!	oti o			25°C	70	93		
k _{SVR}	Supply-voltage rejection r. (ΔV _{DD} /ΔV _{DD})	aแ0	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB
	, DD: DD/				70°C	60	94		
			Vo = 5 V	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	25°C		285	600	
IDD			$V_O = 5 V$, V	V _{IC} = 5 V,	0°C		345	800	μΑ
		No load		70°C		220	560		

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER		TEST CONDITI	ons	TA	TL TL(C	UNIT	
						MIN	TYP	MAX	
					25°C		0.43		
				$V_{I(PP)} = 1 V$	0°C		0.46		
SR	Slow rate at unity gain	$R_L = 100 \text{ k}\Omega$,	$C_L = 20 pF$,		70°C		0.36		\//uc
SK	Slew rate at unity gain	See Figure 1			25°C		0.40	V/μs	
				$V_{I(PP)} = 2.5 V$	0°C		0.43		
					70°C		0.34		
V _n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		32		nV/√ Hz
		., .,			25°C		55		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega$,	0°C		60		kHz
		occ rigure			70°C		50		
					25°C		525		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		600		MHz
					70°C		400		
		V 40V	, ,	0 00 - 5	25°C		40°		
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	0°C		41°		
		galoo			70°C		39°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER		TEST CONDITION	ons	TA	TLO	C25M2C C25M2A C25M2B	C	UNIT
						MIN	TYP	MAX	
					25°C		0.62		
				V _{I(PP)} = 1 V	0°C	0.67 0.51 0.56			
SR	Slow rate at unity gain	$R_L = 100 \text{ k}\Omega$	$C_L = 20 pF$,		70°C				\//uo
J SK	Slew rate at unity gain	See Figure 1			25°C				V/μs
				V _{I(PP)} = 5.5 V	0°C	0.61			
					70°C		0.46		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		32		nV/√ Hz
		., .,		5 400 1 0	25°C		35		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega$,	0°C		40		kHz
		occ rigure r			70°C		30		
					25°C		635		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 3	0°C		710		MHz
	- ,				70°C		510		
		V 40V	(5	0 00 - 5	25°C		43°		
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	0°C		44°		
	-	Seeguio o			70°C		42°		

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electrical characteristics, $V_{DD} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	Т	LC252	Y	Т	LC25L2	Υ	TL	C25M2	Υ	UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_O = 1.4 \text{ V}, V_{IC} = 0 \text{ V}, \\ R_S = 50 \Omega, \text{See Note 6}$		1.1	10		1.1	10		1.1	10	mV
αγιο	Average temperature coefficient of input offset voltage			1.8			1.1			1.7		μV/°C
IIO	Input offset current (see Note 4)	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$		0.1	60		0.1	60		0.1	60	pA
I _{IB}	Input bias current (see Note 4)	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$		0.6	60		0.6	60		0.6	60	pA
VICR	Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		٧
Vон	High-level output voltage	V _{ID} = 100 mV, See Note 6	3.2	3.8		3.2	4.1		3.2	3.9		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV}, I_{OL} = 0$		0	50		0	50		0	50	mV
AVD	Large-signal differential voltage amplification	V _O = 0.25 V, See Note 6	5	23		50	700		25	170		V/mV
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min	65	80		65	94		65	91		dB
ksvr	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 5 V to 10 V, V _O = 1.4 V	65	95		70	97		70	93		dB
I _{DD}	Supply current	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$, No load		1.4	3.2		0.02	0.034		0.21	0.56	mA

operating characteristics, V_{DD} = 5 V, T_A = 25°C

	PARAMETER	TEST CO	NDITIONS	Т	LC252	1	TI	LC25L2	Υ	TL	.C25M2	Υ	UNIT
'	FARAMETER	1231 00	NDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	Slew rate at	$C_L = 20 \text{ pF}, V_{I(PP)} = 1 \text{ V}$			3.6			0.03			0.43		V/us
	unity gain	See Note 6	$V_{I(PP)} = 2.5 V$		2.9			0.03			0.40		ν/μ5
٧n	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		2.5			68			32		nV√/ Hz
ВОМ	Maximum output- swing bandwidth	$V_O = V_{OH}$, $R_L = 10 \text{ k}\Omega$	C _L = 20 pF,		320			5			55		kHz
В ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		1.7			0.085			0.525		MHz
φm	Phase margin	$f = B_1,$ $C_L = 20 pF$	V _I = 10 mV,		46°			34°			40°		

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. For low-bias mode, R_L = 1 $M\Omega$; for medium-bias mode, R_L = 100 $k\Omega$, and for high-bias mode, R_L = 10 $k\Omega$.



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PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC252, TLC25L2, and TLC25M2 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

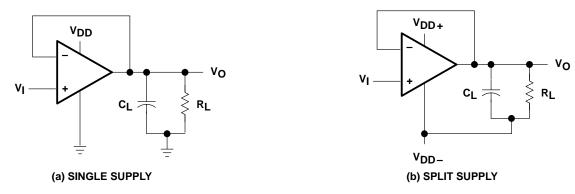


Figure 1. Unity-Gain Amplifier

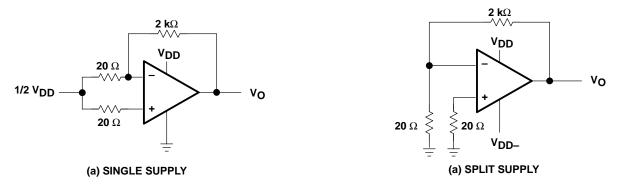


Figure 2. Noise-Test Circuit

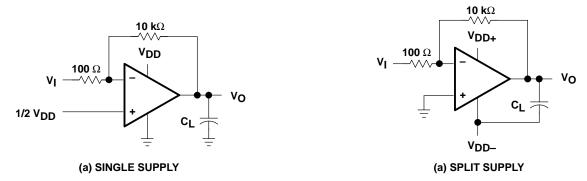


Figure 3. Gain-of-100 Inverting Amplifier

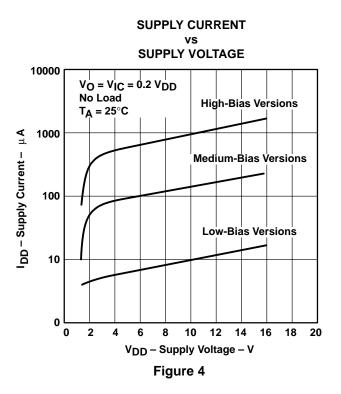


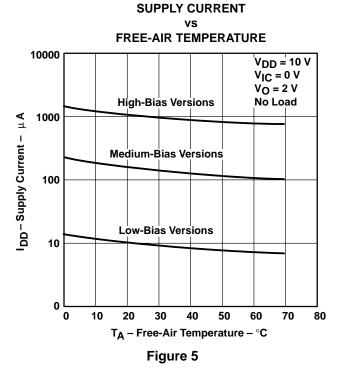
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TYPICAL CHARACTERISTICS

Table of Graphs

				FIGURE
IDD	Supply current		vs Supply voltage vs Free-air temperature	4 5
		Low bias	vs Frequency	6
AVD	Large-signal differential voltage amplification	Medium bias	vs Frequency	7
		High bias	vs Frequency	8
		Low bias	vs Frequency	6
	Phase shift	Medium bias	vs Frequency	7
		High bias	vs Frequency	8





TYPICAL CHARACTERISTICS

LOW-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

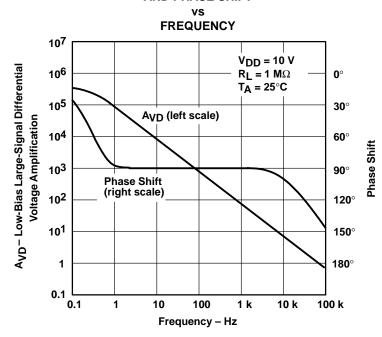


Figure 6

MEDIUM-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

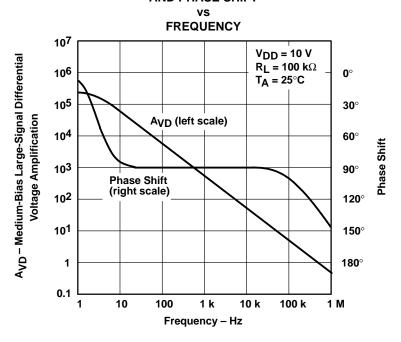


Figure 7



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TYPICAL CHARACTERISTICS

HIGH-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

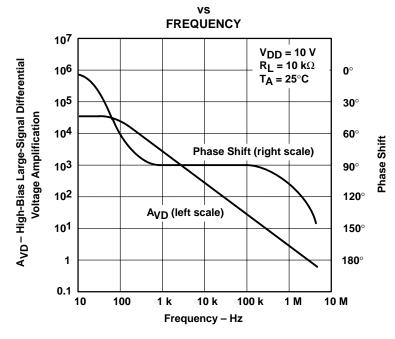


Figure 8

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APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNPN structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifier supplies should be applied simultaneously with, or before, application of any input signals.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD} –/GND.

supply configurations

Even though the TLC252/25_2C series is characterized for single-supply operation, it can be used effectively in a split-supply configuration if the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

The user is cautioned that whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup, as well as excessive dc leakages.







2-Sep-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLC252ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	252AC	Samples
TLC252ACP	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI			
TLC252BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC252BCP	Samples
TLC252CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	252C	Samples
TLC252CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	252C	Samples
TLC252CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	252C	Samples
TLC252CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	252C	Samples
TLC252CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC252CP	Samples
TLC252CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC252CP	Samples
TLC252CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P252	Samples
TLC25L2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25L2AC	Samples
TLC25L2BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25L2BC	Samples
TLC25L2BCDR	PREVIEW	SOIC	D	8		TBD	Call TI	Call TI			
TLC25L2BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC25L2BC	Samples
TLC25L2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25L2C	Samples
TLC25L2CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25L2C	Samples
TLC25L2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		25L2C	Samples
TLC25L2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type		TLC25L2CP	Samples



PACKAGE OPTION ADDENDUM

2-Sep-2016

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLC25L2CPSR	OBSOLETE	so	PS	8		TBD	Call TI	Call TI			
TLC25L2CPSRG4	OBSOLETE	SO	PS	8		TBD	Call TI	Call TI			
TLC25M2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25M2AC	Samples
TLC25M2ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC25M2AC	Samples
TLC25M2BCD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI			
TLC25M2BCP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI			
TLC25M2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25M2C	Samples
TLC25M2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	25M2C	Samples
TLC25M2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC25M2CP	Samples
TLC25M2CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC25M2CP	Samples
TLC25M2CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI	0 to 70	<u> </u>	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

2-Sep-2016

- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

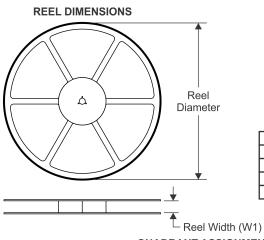
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC252CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC252CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC252CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC25L2CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC25M2CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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*All dimensions are nominal

7 til differencierie die fiermina											
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)				
TLC252CDR	SOIC	D	8	2500	340.5	338.1	20.6				
TLC252CDR	SOIC	D	8	2500	367.0	367.0	38.0				
TLC252CPWR	TSSOP	PW	8	2000	367.0	367.0	35.0				
TLC25L2CDR	SOIC	D	8	2500	340.5	338.1	20.6				
TLC25M2CDR	SOIC	D	8	2500	340.5	338.1	20.6				

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